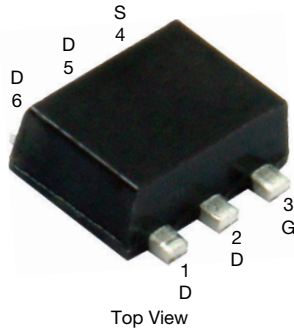


## N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) MAX.	I <sub>D</sub> (A)	Q <sub>g</sub> (TYP.)
30	0.142 at V <sub>GS</sub> = 10 V	1.02	1.5
	0.154 at V <sub>GS</sub> = 4 V	0.98	
	0.195 at V <sub>GS</sub> = 2.5 V	0.87	

**SC-89 Single (6 leads)**


Top View

**Marking Code:** D

**Ordering Information:**

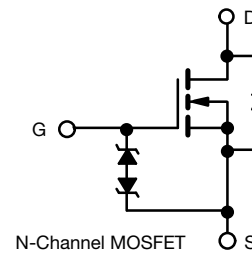
Si1078X-T1-GE3 (lead (Pb)-free and halogen-free)

**FEATURES**

- TrenchFET® power MOSFET
- 100 % R<sub>g</sub> tested
- Typical ESD performance 1400 V
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**
**APPLICATIONS**

- Load switch for portable devices



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	± 12	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	1.02 <sup>a, b</sup>	A
	T <sub>A</sub> = 70 °C		0.82 <sup>a, b</sup>	
Pulsed Drain Current (t = 100 μs)		I <sub>DM</sub>	6	
Continuous Source-Drain Diode Current	T <sub>A</sub> = 25 °C	I <sub>S</sub>	0.2 <sup>a, b</sup>	W
Maximum Power Dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	0.24 <sup>a, b</sup>	
	T <sub>A</sub> = 70 °C		0.15 <sup>a, b</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient <sup>a, c</sup>	t ≤ 5 s	R <sub>thJA</sub>	440	530	°C/W
	Steady State		540	650	

**Notes**

- Surface mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under steady state conditions is 650 °C/W.



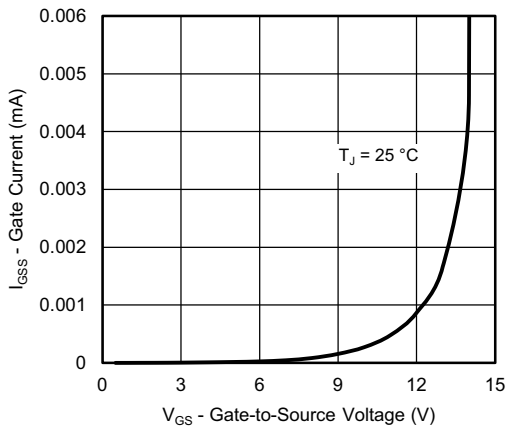
SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = 250 μA	-	36.7	-	mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>		-	-2.8	-	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	0.6	-	1.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V	-	-	± 20	μA
		V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 4.5 V	-	-	± 1	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	-	-	1	
		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C	-	-	10	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = ≥ 5 V, V <sub>GS</sub> = 10 V	6	-	-	A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1 A	-	0.118	0.142	Ω
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 1 A	-	0.128	0.154	
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 0.5 A	-	0.150	0.195	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 1 A	-	5.5	-	S
<b>Dynamic <sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	-	110	-	pF
Output Capacitance	C <sub>oss</sub>		-	21	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	11	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1 A	-	3	6	nC
		V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 1 A	-	1.5	3	
Gate-Source Charge	Q <sub>gs</sub>		-	0.2	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	0.42	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz	1.04	5.2	5.6	Ω
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 18.9 Ω I <sub>D</sub> ≅ 0.8 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω	-	8	16	ns
Rise Time	t <sub>r</sub>		-	25	38	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	23	35	
Fall Time	t <sub>f</sub>		-	23	35	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 15 V, R <sub>L</sub> = 18.9 Ω I <sub>D</sub> ≅ 0.8 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω	-	5	10	
Rise Time	t <sub>r</sub>		-	23	35	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	10	20	
Fall Time	t <sub>f</sub>		-	35	53	
<b>Drain-Source Body Diode Characteristics</b>						
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>		-	-	6	A
Body Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.8 A	-	0.75	1.2	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2 A, di/dt = 100 A/μs	-	12	20	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>		-	4	8	nC
Reverse Recovery Fall Time	t <sub>a</sub>		-	7	-	ns
Reverse Recovery Rise Time	t <sub>b</sub>		-	5	-	

**Notes**

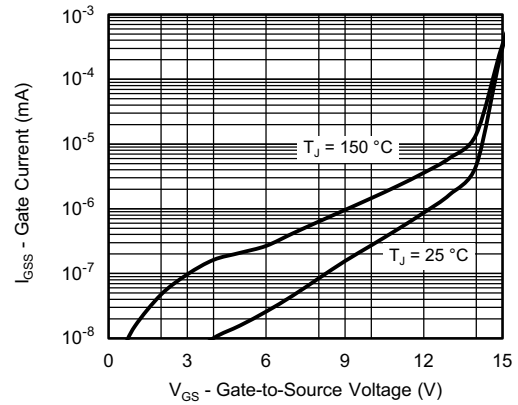
- a. Pulse test; pulse width ≤ 100 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

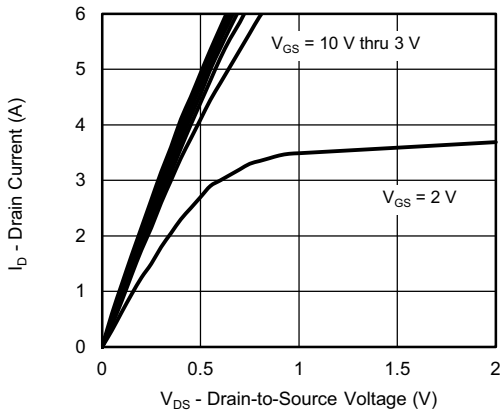
**TYPICAL CHARACTERISTICS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



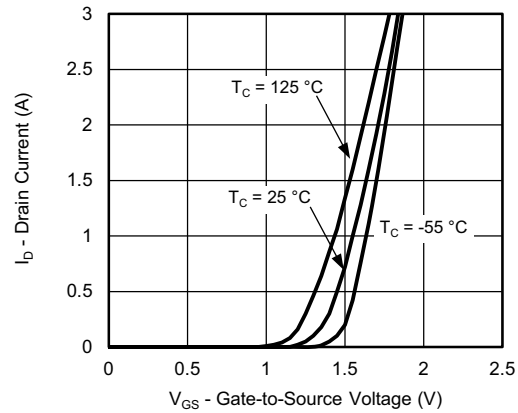
**Gate Current vs. Gate-to-Source Voltage**



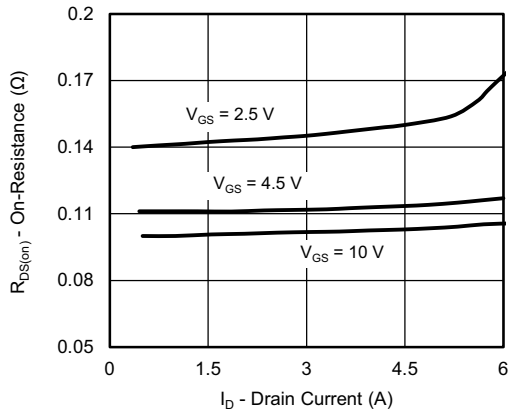
**Gate Current vs. Gate-to-Source Voltage**



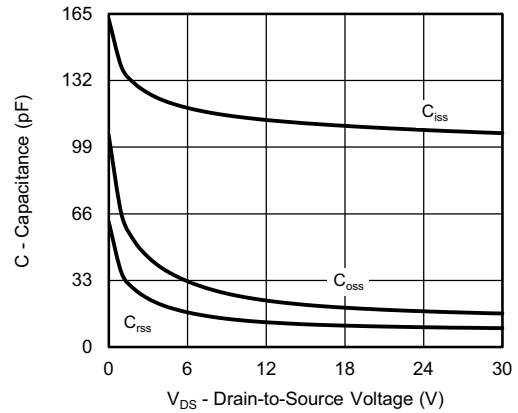
**Output Characteristics**



**Transfer Characteristics**



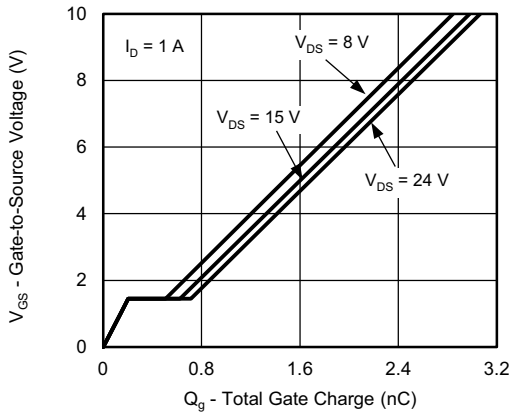
**On-Resistance vs. Drain Current**



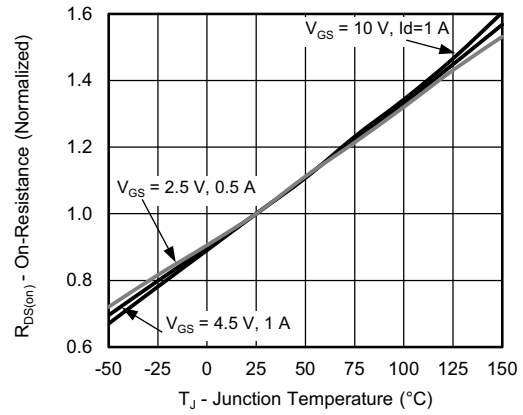
**Capacitance**



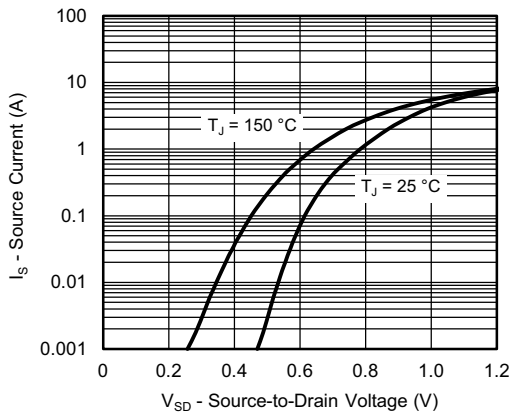
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



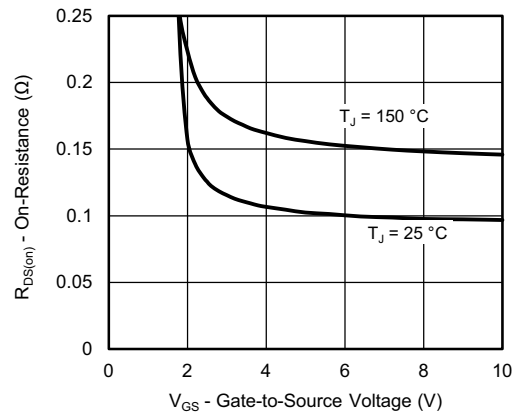
Gate Charge



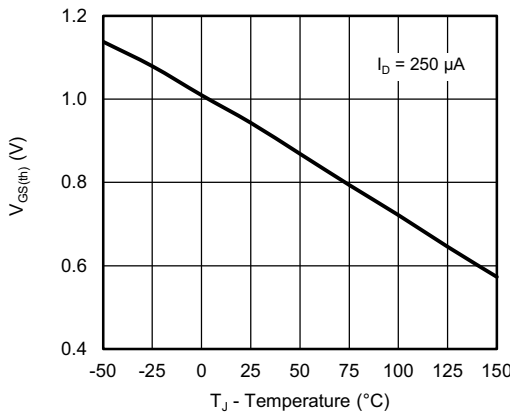
On-Resistance vs. Junction Temperature



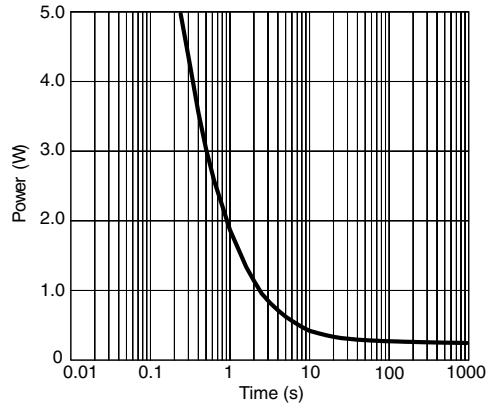
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



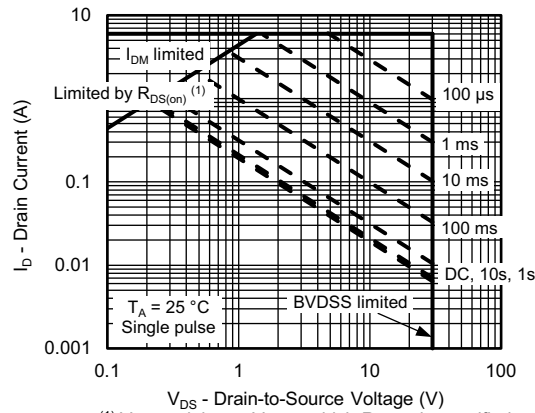
Threshold Voltage



Single Pulse Power, Junction-to-Ambient

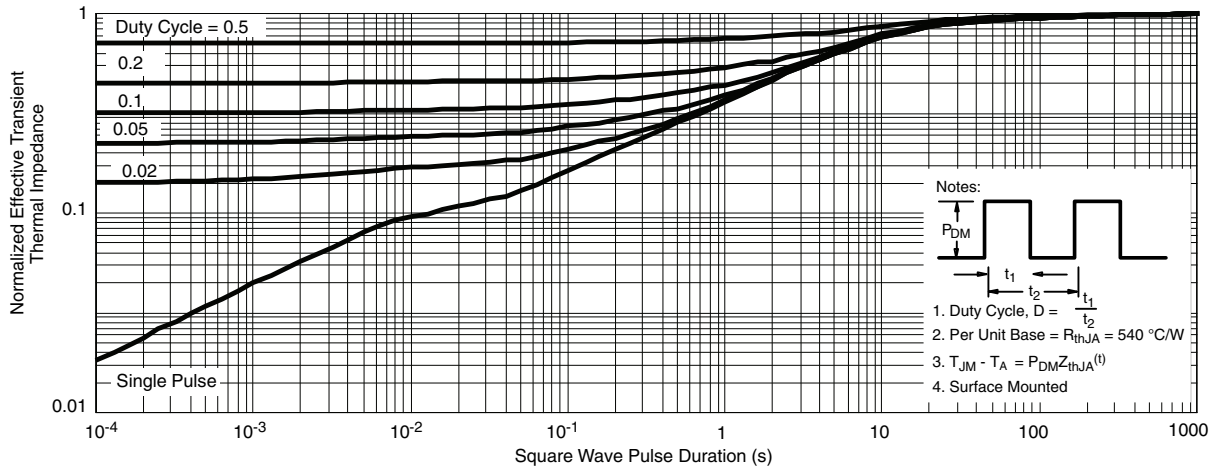


TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



<sup>(1)</sup> V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified

Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

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### SC-89 6-Leads (SOT-563F)



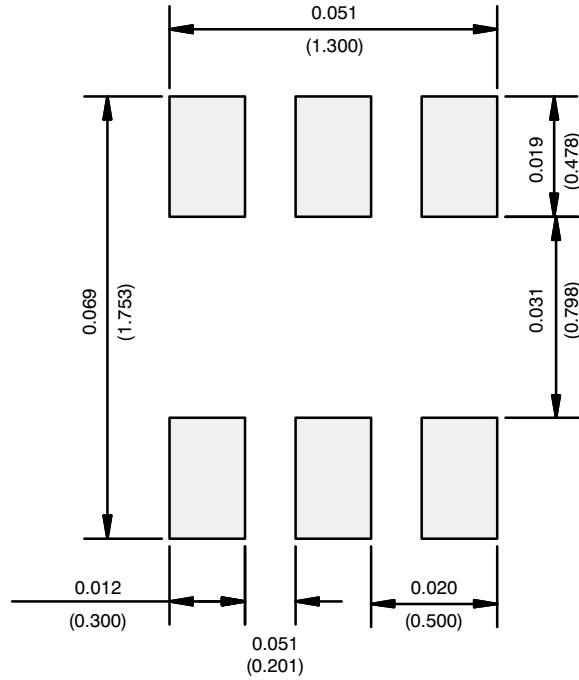
**Notes**

- 1. Dimensions in millimeters.
- ⚠ Dimension D does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.
- ⚠ Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.
- ⚠ Datums A, B and D to be determined 0.10 mm from the lead tip.
- ⚠ Terminal numbers are shown for reference only.
- ⚠ These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.56	0.58	0.60
A1	0	0.02	0.10
b	0.15	0.22	0.30
c	0.10	0.14	0.18
D	1.50	1.60	1.70
E	1.50	1.60	1.70
E1	1.15	1.20	1.25
e	0.45	0.50	0.55
e1	0.95	1.00	1.05
L	0.25	0.35	0.50
L1	0.10	0.20	0.30

C14-0439-Rev. C, 11-Aug-14  
DWG: 5880

RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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